

T-41-89

# Photon Coupled Isolator H11L1, H11L2, H11L3

## Ga As Infrared Emitting Diode & Microprocessor Compatible Schmitt Trigger

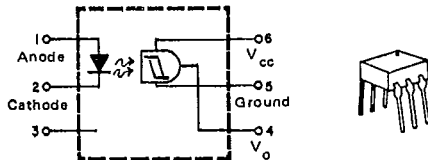
The GE Solid State H11L series has a gallium arsenide, infrared emitting diode optically coupled across an isolating medium to a high speed integrated circuit detector. The output incorporates a Schmitt Trigger which provides hysteresis for noise immunity and pulse shaping. The detector circuit is optimized for simplicity of operation and utilizes an open collector output for maximum application flexibility. These devices are mounted in dual-in-line packages. These devices are also available in Surface-Mount packaging.

### FEATURES

- Free from latch up and oscillation throughout voltage and temperature ranges
- High data rate, 1 MHz typical (NRZ)
- Microprocessor compatible drive
- Logic compatible output sinks 16 milliamperes at 0.4 volts maximum
- High isolation between input and output
- Guaranteed On/Off threshold hysteresis
- High common mode rejection ratio
- Fast switching;  $t_{rise}, t_{fall} = 100$  nanoseconds typical
- Wide supply voltage capability, compatible with all popular logic systems

### MECHANICAL SPECIFICATIONS

- Plastic 6 PIN dual in line package, tin plated leads
- Lead orientation as shown:



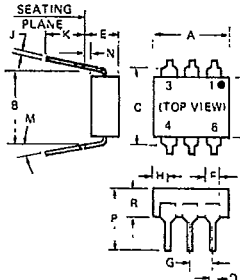
absolute maximum ratings: (25°C)

INFRARED EMITTING DIODE		
Power Dissipation	*100	milliwatts
Forward Current (Continuous)	60	milliamperes
Reverse Voltage	6	volts
*Derate 1.33 mW/°C above 25°C ambient.		

PHOTO DETECTOR		
Power Dissipation	**150	milliwatts
V <sub>45</sub> Allowed Range	0 to 16	volts
V <sub>65</sub> Allowed Range	0 to 16	volts
I <sub>4</sub> Output Current	50	milliamperes
**Derate 2.0 mW/°C above 25°C ambient.		

### APPLICATIONS

- Logic to logic isolator
- Programmable current level sensor
- Line receiver – eliminates noise and transient problems
- Logic level shifter – couples TTL to CMOS
- A.C. to TTL conversion – square wave shaping
- Digital programming of power supplies
- Interfaces computers with peripherals



SYMBOL	MILLIMETERS		INCHES		NOTES
	MIN.	MAX.	MIN.	MAX.	
A	8.38	8.89	.330	.350	
B	7.62 REF		.300 REF.		1
C		8.84		.340	2
D	4.06	5.08	.161	.020	
E		5.08		.200	3
F	1.01	1.78	.040	.070	
G	2.28	2.80	.090	.110	
H		2.16		.085	4
J	2.03		.080	.012	
K	2.54		.100		
M		.15		.15	
N	.381		.015		
P		.953		.375	
Q	2.92	3.43	.115	.135	
S	6.10	6.86	.240	.270	

NOTES  
1 INSTALLED POSITION LEAD CENTERS  
2 OVERALL INSTALLED DIMENSION  
3 THESE MEASUREMENTS ARE MADE FROM THE SEATING PLANE 4 FOUR PLACES

TOTAL DEVICE	
Storage Temperature	-55°C to +150°C
Operating Temperature	-55°C to +100°C
Lead Soldering Time (at 260°C)	10 seconds
Surge Isolation Voltage (Input to Output)	
3535 V <sub>(peak)</sub>	2500 V <sub>(RMS)</sub>
Steady-State Isolation Voltage (Input to Output)	
3180 V <sub>(peak)</sub>	2250 V <sub>(RMS)</sub>

Ⓜ Covered under U.L. component recognition program, reference file E51868

VDE Approved to 0883/6.80 0110b Certificate # 35025

HARRIS SEMICONDUCTOR SECTOR 37E D ■ 4302271 0027209 1 ■ HAS

electrical characteristics: (0-70°C)

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INFRARED EMITTING DIODE				PHOTO DETECTOR							
	MIN.	TYP.	MAX.	UNITS		MIN.	TYP.	MAX.	UNITS		
Forward Voltage $I_F = 10 \text{ mA}$ $I_F = 0.3 \text{ mA}$	$V_F$	- 0.75	1.10 0.95	1.50 -	volts volts	Operating Voltage Range $V_{CC}$	3	-	15	volts	
Reverse Current ( $V_R = 3 \text{ V}$ )	$I_R$	-	-	10	micro-ampere	Supply Current ( $I_F = 0, V_{CC} = 5 \text{ V}$ )	$I_{6(\text{off})}$	-	1.0	5.0	milli-ampere
Capacitance ( $V = 0, f = 1 \text{ MHz}$ )	$C_J$	-	-	100	picofarads	Output Current, High ( $I_F = 0, V_{CC} = V_o = 15 \text{ V}$ )	$I_{OH}$	-	-	100	micro-ampere

coupled electrical characteristics (0-70°C)

	MIN.	TYP.	MAX.	UNITS
Supply Current ( $I_F = 10 \text{ mA}, V_{CC} = 5 \text{ V}$ )	-	1.6	5.0	milliampere
Output Voltage, Low ( $R_{64} = 270 \Omega, V_{CC} = 5 \text{ V}, I_F = I_{F(\text{on})} \text{ Max}$ )	-	0.2	0.4	volts
Turn-On Threshold Current ( $R_{64} = 270 \Omega, V_{CC} = 5 \text{ V}$ )				
				H11L1
				H11L2
				H11L3
Turn-Off Threshold Current ( $R_{64} = 270 \Omega, V_{CC} = 5 \text{ V}$ )				
				$I_{F(\text{off})}$
Hysteresis Ratio ( $R_{64} = 270 \Omega, V_{CC} = 5 \text{ V}$ )	0.50	0.75	0.90	-

switching characteristics (25°C) H11L1

SWITCHING SPEED		MIN.	TYP.	MAX.	UNITS
$R_E = 1200 \Omega, C = 0$					
Turn-On Time	$t_{on}$	-	1.0	-	$\mu\text{sec.}$
Fall Time	$t_f$	-	0.1	-	$\mu\text{sec.}$
Turn-Off Time	$t_{off}$	-	2.0	-	$\mu\text{sec.}$
Rise Time	$t_r$	-	0.1	-	$\mu\text{sec.}$
$R_E = 1200 \Omega, C = 270 \text{ pF}, f \leq 100 \text{ KHz}, t_p \geq 1 \mu\text{sec}$					
Turn-On Time	$t_{on}$	-	0.65	-	$\mu\text{sec.}$
Fall Time	$t_f$	-	0.05	-	$\mu\text{sec.}$
Turn-Off Time	$t_{off}$	-	1.20	-	$\mu\text{sec.}$
Rise Time	$t_r$	-	0.07	-	$\mu\text{sec.}$
Data Rate (NRZ)		-	1.0*	-	MHz
<u>Overdrive Switching</u>					
$V_{IN} = 5 \text{ V DC}, R_E = 75 \Omega, C = 0, V_{CC} = 5 \text{ V}, R_L = 270 \Omega$					
Turn-Off Time	$t_{off}$	-	-	10	$\mu\text{sec.}$

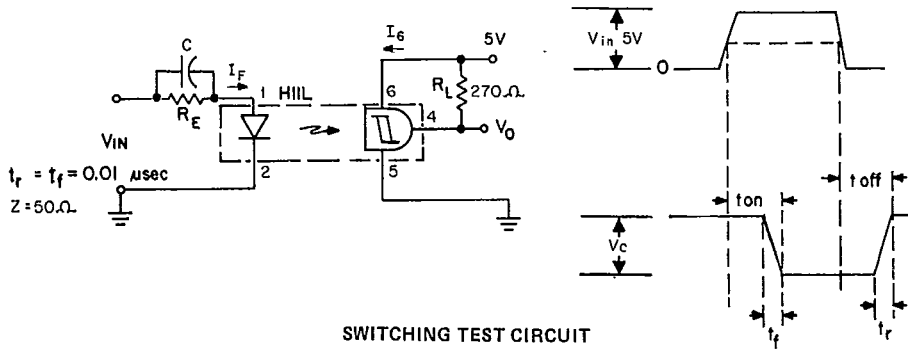
\*Maximum data rate will vary depending on the bias conditions and is usually highest when  $R_E$  and C are matched to  $I_{F(\text{on})}$  and  $V_{CC}$  is between 3 and 5V, with this optimized bias, most units will operate at over 1.5 MHz, NRZ.

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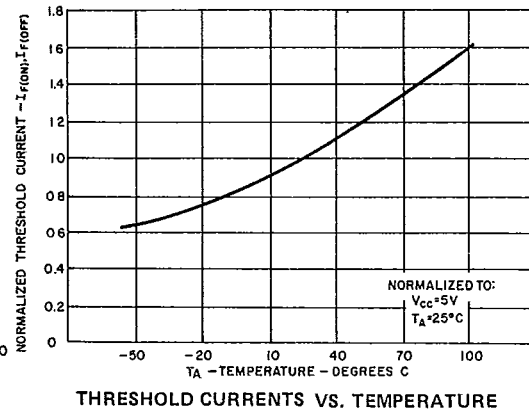
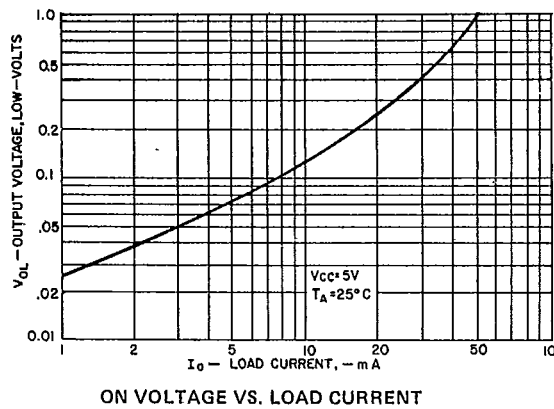
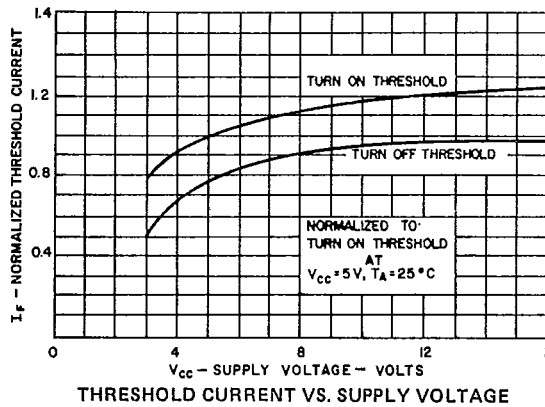
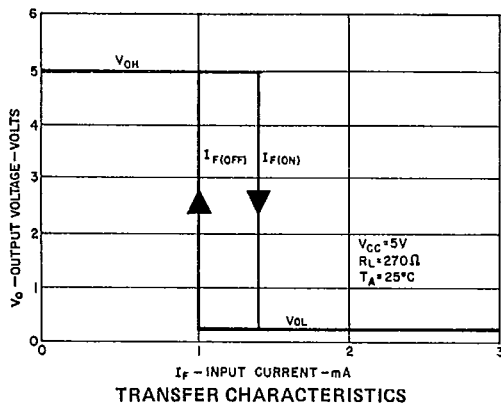
H11L1, H11L2, H11L3

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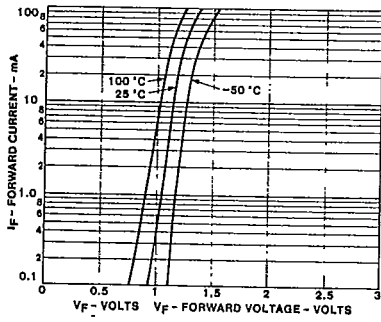
switching characteristics (25°C)



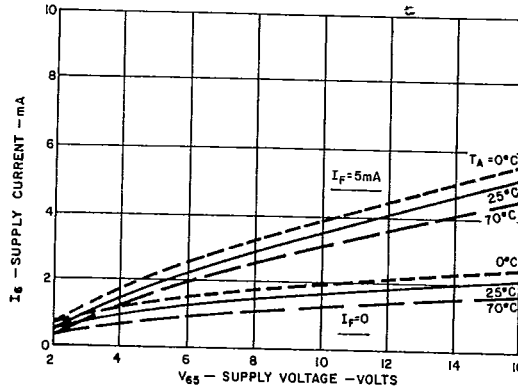
TYPICAL CHARACTERISTICS



HARRIS SEMICONDUCTOR SECTOR 37E D 430227J 0027210 8 HAS

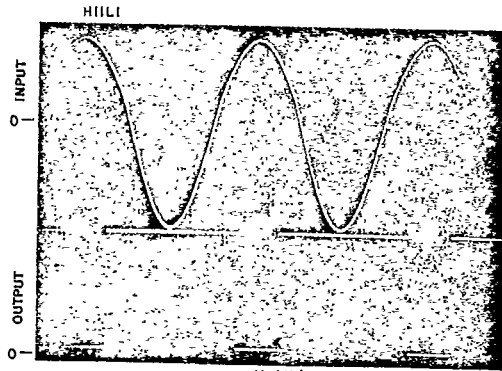


FORWARD VOLTAGE VS. FORWARD CURRENT

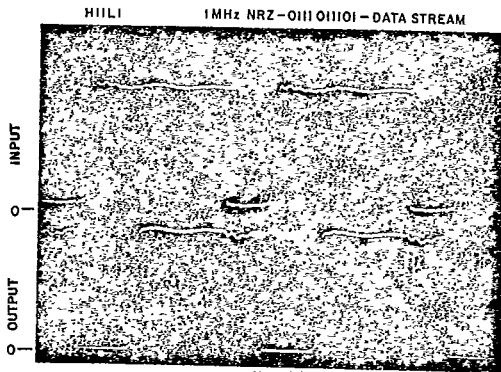


SUPPLY CURRENT VS. SUPPLY VOLTAGE

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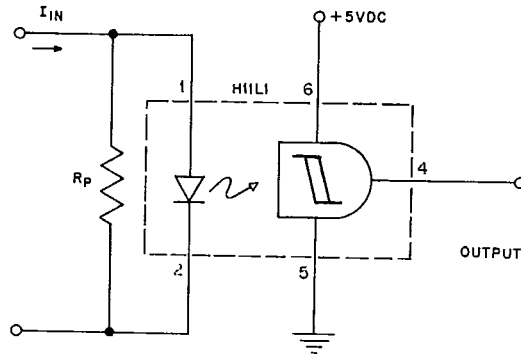
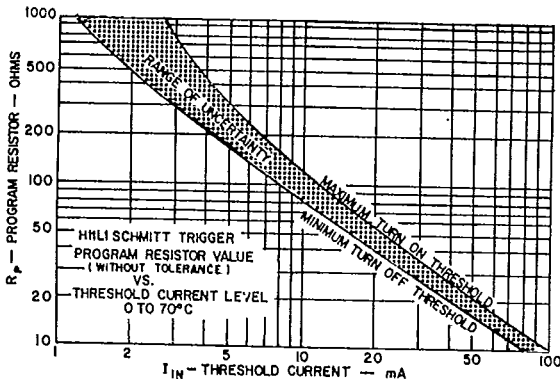


V = 2V / DIV  
H = 5ms / DIV  
 $R_L = 270\Omega$   
 $R_E = 1200\Omega$   
C = 0



V = 2V / DIV  
H = 1μS / DIV  
 $R_L = 270\Omega$   
 $R_E = 1.2K\Omega$   
C = 270pf

TYPICAL APPLICATION



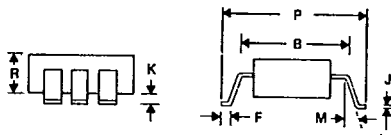
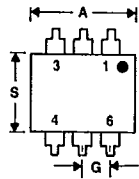
PROGRAMMABLE CURRENT THRESHOLD SENSING CIRCUIT

PLEASE NOTE. THE INFORMATION INCLUDED IN THIS SPECIFICATION HAS BEEN CAREFULLY CHECKED AND IS BELIEVED TO BE RELIABLE, HOWEVER, NO RESPONSIBILITY IS ASSUMED FOR INACCURACIES.

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T-91-20

# Surface-Mount Optoisolators



Surface-mount packaging for the entire 6-pin DIP optoisolator line!

Add the "SMA" or "SMB" suffix to any 6-pin optoisolator part number when ordering.

**DIMENSIONAL OUTLINE NO. 298**  
All Surface-Mount Types

**SMB (Standard)**  
Surface-Mount Package

SYMBOL	INCHES		MILLIMETERS		NOTES
	MIN.	MAX.	MIN.	MAX.	
A	0.330	0.350	8.38	8.89	
B	0.330 REF		8.38 REF		
F	0.020	0.040	0.508	1.02	
J	0.008	0.012	0.203	0.305	
K	0.0040	0.0098	0.102	0.249	
M	—	15°	—	15°	
P	0.375	0.395	9.53	10.03	
R	0.115	0.135	2.92	3.43	
S	0.240	0.270	6.10	6.86	
Coplanarity	0	0.002	0	0.051	1

92CS-42862

1. Coplanarity is the distance from a plane, defined by the end of the three longest legs to the end of the shortest leg.

**SMA (Low Profile)**  
Surface-Mount Package

SYMBOL	INCHES		MILLIMETERS		NOTES
	MIN.	MAX.	MIN.	MAX.	
A	0.330	0.350	8.38	8.89	
B	0.330 REF		8.38 REF		
F	0.020	0.040	0.508	1.02	
J	0.008	0.012	0.203	0.305	
K	0.0005	0.0040	0.013	0.102	
M	—	15°	—	15°	
P	0.373	0.393	9.47	9.98	
R	0.115	0.135	2.92	3.43	
S	0.240	0.270	6.10	6.86	
Coplanarity	0	0.002	0	0.051	1

92CS-42861

1. Coplanarity is the distance from a plane, defined by the end of the three longest legs to the end of the shortest leg.

